

2SA1020

PNP SILICON TRANSISTOR

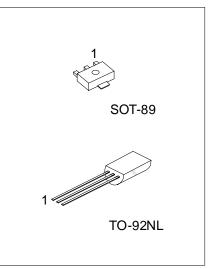
SILICON PNP EPITAXIAL TRANSISTOR

DESCRIPTION

The UTC 2SA1020 is designed for power amplifier and power switching applications.

FEATURES

*Low collector saturation voltage: V_{CE(SAT)}=-0.5V(max.) (I_C=-1A) *High speed switching time: t_{STG}=1.0µs(Typ.) *Complement to UTC 2SC2655



*Pb-free plating product number:2SA1020L

ORDERING INFORMATION

Order Number		Dealiana	Pin Assignment			Dealing	
Normal	Lead Free Plating	Package	1	2	3	Packing	
2SA1020-x-AB3-R	2SA1020L-x-AB3-R	SOT-89	В	С	Е	Tape Reel	
2SA1020-x-T9N-B	2SA1020L-x-T9N-B	TO-92NL	Е	С	В	Tape Box	
2SA1020-x-T9N-K	2SA1020L-x-T9N-K	TO-92NL	Е	С	В	Bulk	

(2) AB3: SOT-89	(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AB3: SOT-89, T9N: TO-92NL		
(3) Rank (3) x: refer to Cla), 19N: 1O-92NL assification of h _{FE1} Plating, Blank: Pb/Sn		

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V _{CBO}	-50	V	
Collector-Emitter Voltage		V _{CEO}	-50	V	
Emitter-Base Voltage		V _{EBO}	-5	V	
Collector Current		lc	-2	А	
Callester Dewer Dissinction	TO-92NL	Б	900	mW	
Collector Power Dissipation	SOT-89	P _C	500	mW	
Junction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
					IIF	IVIAA	
Collector to Emitter Breakdown Voltage		BV _{CEO}	Ic=-10mA, I _B =0	-50			V
Collector Cut-off Current		I _{CBO}	V_{CB} =-50V, I _E =0			-1.0	μA
Emitter Cut-off Current		I _{EBO}	V_{EB} =-5V, I_{C} =0			-1.0	μA
DC Current Gain		h _{FE1}	V _{CE} =-2V, I _C =-0.5A	70		240	
		h _{FE2}	V _{CE} =-2V, I _C =-1.5A	40			
Collector to Emitter Saturation Voltage		V _{CE(SAT)}	Ic=-1A, I _B =-0.05A			-0.5	V
Base to Emitter Saturation Voltage		V _{BE(SAT)}	Ic=-1A, I _B =-0.05A			-1.2	V
Transition Frequency		f⊤	V _{CE} =-2V, Ic=-0.5A		100		MHz
Collector Output Capacitance		Cob	V _{CB} =-10V, I _E =0, f=1MHz		40		pF
Switching Time	Turn-on Time	t _{ON}	INPUT 1B2 OUTPUT		0.1		μS
	Storage Time	t _{STG}			1.0		μS
	Fall Time	t _F	$ \begin{array}{c} I_{B1} \blacksquare \\ -I_{B1} = I_{B2} = 0.05 A \\ DUTY CYCLE \le 1\% \end{array} \right) \begin{array}{c} U_{CC} = -30V \\ V_{CC} = -30V \\ U_{CC} = -30V \\ U_{CC$		0.1		μs

CLASSIFICATION OF h_{FE1}

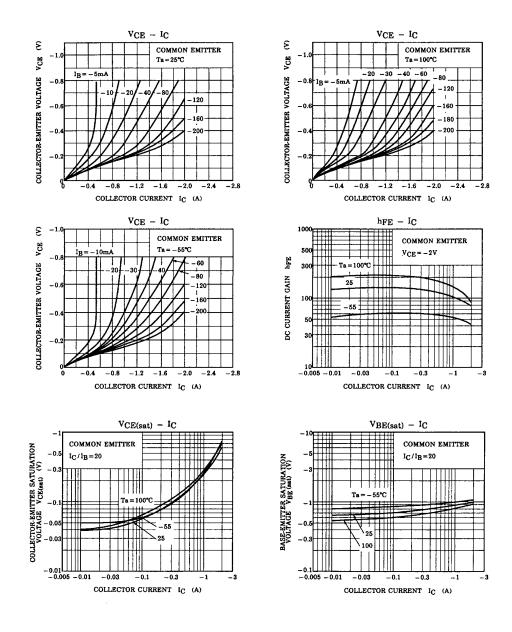
RANK	0	Y
RANGE	70 - 140	120 - 240



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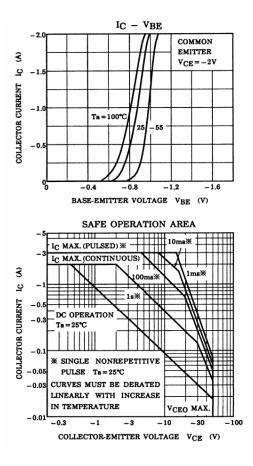
TYPICAL CHARACTERISTICS

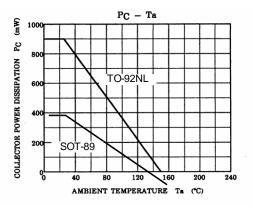




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■ TYPICAL CHARACTERISTICS(Cont.)





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